

C650-30E

Red LED CHIP

<Specifications>

Commodity Type and Physical Characteristics	
Material	InGaAlP
Top Side P(anode)side	Au Alloy/Pad
Bottom Side N(cathode)side	Au Alloy
Electrode Pattern	Fig.1
Chip Size	Fig.2
Chip Thickness	Fig.2
Emission Area	Fig.2

Electro-Optical Characteristics [Ta=25℃]						
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	IF=20mA		1.8	2.2	V
Reverse Current	IR	VR=5V			10	uA
Brightness	IV	IF=20mA		120		mcd
Power Intensity	PO	IF=20mA		3		mW
Peak Wavelength	λP	IF=20mA	640	650	660	nm
Spectral Radiation Bandwidth	Δλ	IF=20mA		15		nm

Die shall be mounted on TO-18 gold header without resin coated.

[Unit:um]

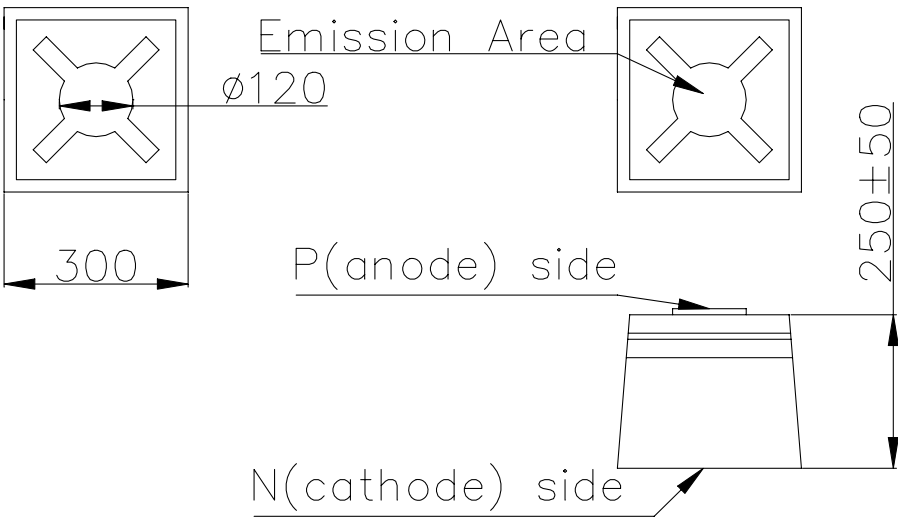


Fig.1 Electrode Pattern

Fig.2 Chip Size and Emission Area